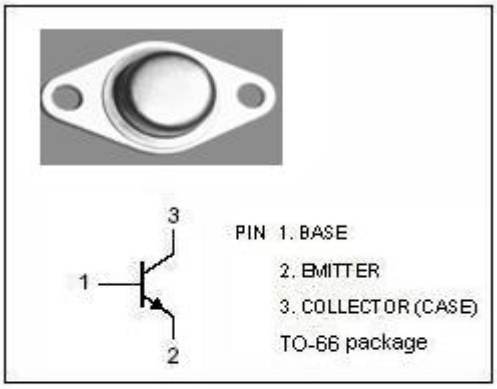
isc Silicon NPN Power Transistor — 2SD546

DESCRIPTION

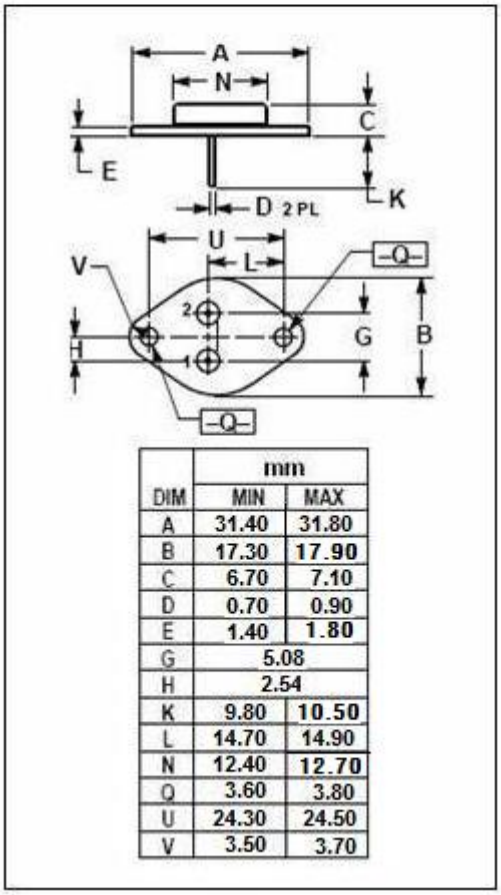
- Continuous Collector Current-I_C= 1A
- Power Dissipation-P_D=30W @T_C= 25℃
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

.



ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	800	V
V_{CEO}	Collector-Emitter Voltage	500	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	1.0	A
P_C	Collector Power Dissipation@T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.90
C	6.70	7.10
D	0.70	0.90
E	1.40	1.80
G	5.08	
H	2.54	
K	9.80	10.50
L	14.70	14.90
N	12.40	12.70
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C=10mA ; I_B=0	500			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 500mA; I_B= 100mA			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 500mA; I_B= 100mA			1.5	V
I_{CBO}	Base Cutoff Current	V_{CE}= 800V; I_B=0			0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C=0			0.1	mA
h_{FE}	DC Current Gain	I_C= 20mA ; V_{CE}= 10V	40		200	
f_T	Transition frequency	I_C= 0.1A ; V_{CE}= 10V		**7**		MHz